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TECHNOLOGY CENTER 2800

IN THE CLAIMS:

Claim 1 has been amended as follows:

1. (Three Times Amended) A fabrication method of a semiconductor device comprising the steps of:
 - forming a first insulation layer over a substrate,
 - introducing impurities into said first insulation layer,
 - forming, in said first insulation layer, a trench extending in a line [in said first insulation layer], and
 - embedding and forming a first conductive layer in said trench extending linearly.